

HAMAMATSU

TECHNICAL DATA

**PHOTOREFLECTOR
P3062-01**

T-41-73

**Photo IC output (digital output), Long focal distance (3mm),
Thin package (4.0 x 4.2 x 1.7mm)**

The P3062-01 is a photoreflector combining a high-power infrared LED and a single chip photo IC consisting of a high-sensitivity photodiode, an amplifier, a schmitt trigger, an output transistor, etc. It features an ultra-compact package measuring 4.0 x 4.2 x 1.7mm. Moreover, since the lens is provided, the focal distance extends to 3mm, so that detection is possible over longer distances.

FEATURES

- Photo IC output (digital output)
- Miniature size : 4.0 x 4.2 x 1.7mm
- Long focal distance : 3mm
- Visible-cut type
- High sensitivity

APPLICATIONS

- Position detection of AF lens
- Detection of light protection notches on floppy disc
- Paper detection in copiers and printers
- Tape-end detection in VTRs and cassette decks

MAXIMUM RATINGS (Ta = 25°C)

Parameters		Symbols	Ratings	Unit
Input	Forward Current	I_F	50	mA
	Reverse Voltage	V_R	5	V
	Power Dissipation	P	75	mW
Output	Supply Voltage	V_{CC}	16	V
	Low Level Output Current	I_{OL}	50	mA
	Power Dissipation	P_O	150	mW
Operating Temperature		T_{opr}	-25 ~ +85	°C
Storage Temperature		T_{stg}	-40 ~ +100	°C
Soldering Temperature		260°C, within 5 seconds		

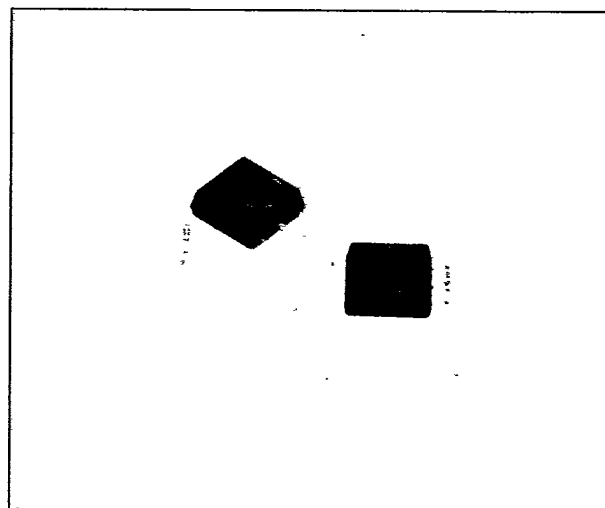
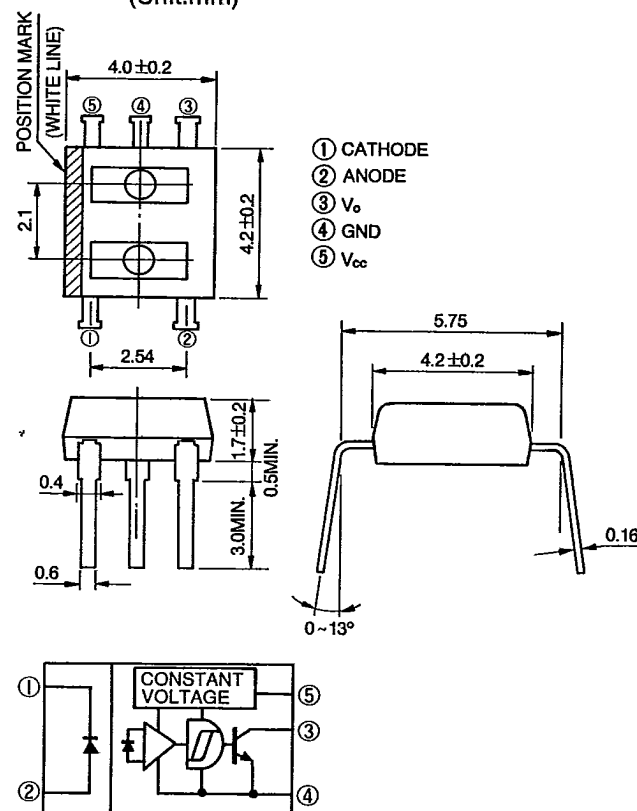


Figure 1: Dimensional Outline and Pin Connection
(Unit:mm)



PHOTOREFLECTOR P3062-01**ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

Parameters		Symbols	Conditions	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V_F	$I_F = 20\text{mA}$	—	1.3	1.6	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Terminal Capacitance	C_t	$V = 0, f = 1\text{kHz}$	—	30	—	pF
Output	Operating Supply Voltage	V_{CC}		4.5	—	16	V
	Low Level Output Voltage	V_{OL}	$V_{CC} = 5\text{V}, I_{OL} = 16\text{mA}, I_F = 0\text{mA}$	—	0.1	0.4	V
	High Level Output Current	I_{OH}	$V_{CC} = V_O = 15\text{V}, I_F = 20\text{mA}$	—	—	100	μA
	Low Level Supply Current	I_{CCL}	$V_{CC} = 5\text{V}, I_F = 0\text{mA}$	—	5.2	12	mA
	High Level Supply Current	I_{CCH}	$V_{CC} = 5\text{V}, I_F = 20\text{mA}$	—	3.2	10	mA
Transfer Characteristics	L→H Threshold Input Current (1)	I_{FLH}	$V_{CC} = 5\text{V}, R_L = 280\Omega, d = 3\text{mm}$ Reflected surface = white paper (reflectivity 90% min.)	—	—	20	mA
	Hysteresis		I_{FHL}/I_{FLH}	—	0.9	—	—
	L→H Propagation Delay Time (2)	t_{PLH}	$V_{CC} = 5\text{V}, I_F = 20\text{mA}$ $R_L = 280\Omega$	—	2.0	9	μs
	H→L Propagation Delay Time (2)	t_{PHL}		—	4.0	15	μs
	Rise Time (2)	t_r		—	0.15	—	μs
	Fall Time (2)	t_f		—	0.05	—	μs

(1) Connect a capacitor of more than $0.01\mu\text{F}$ between V_{CC} and GND.

(2) Response Time Measuring Circuit

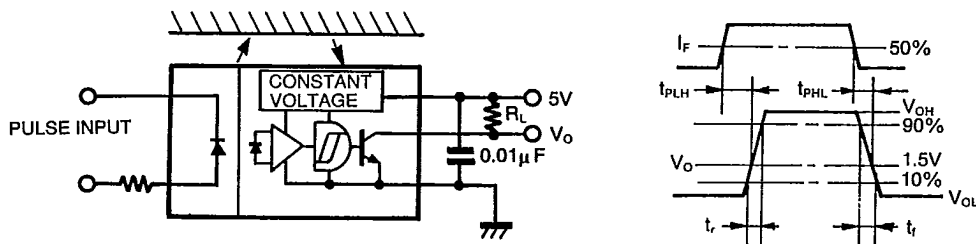


Figure 2: LED Allowable Forward Current vs. Temperature

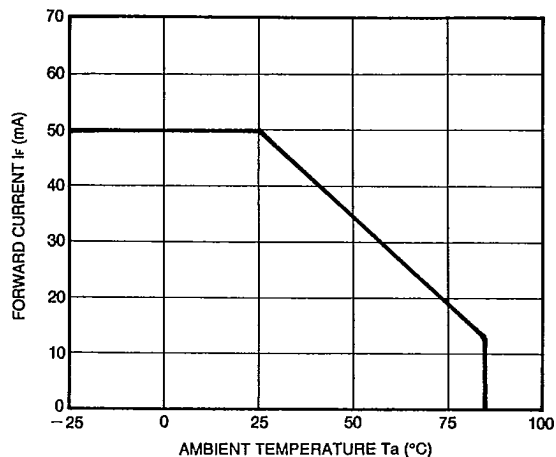


Figure 3: Photo IC Allowable Power Dissipation vs. Temperature

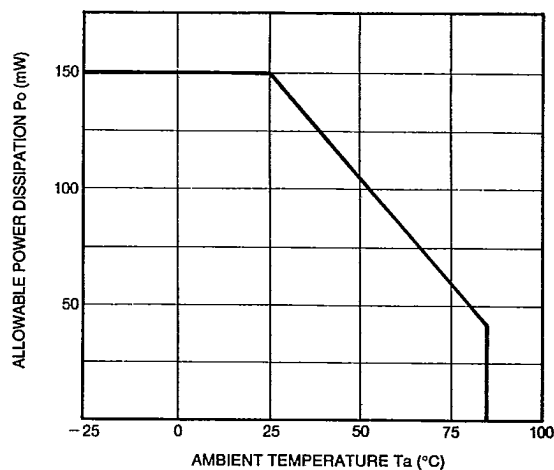


Figure 4: Peak Forward Current vs. Duty Ratio

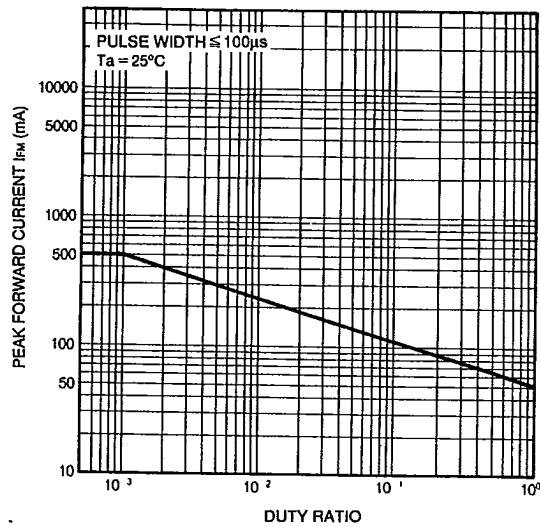


Figure 5: Forward Current vs. Forward Voltage

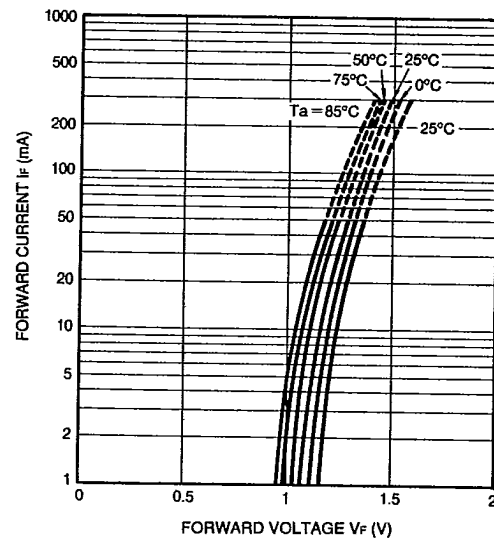


Figure 6: Low Level Output Voltage vs. Output

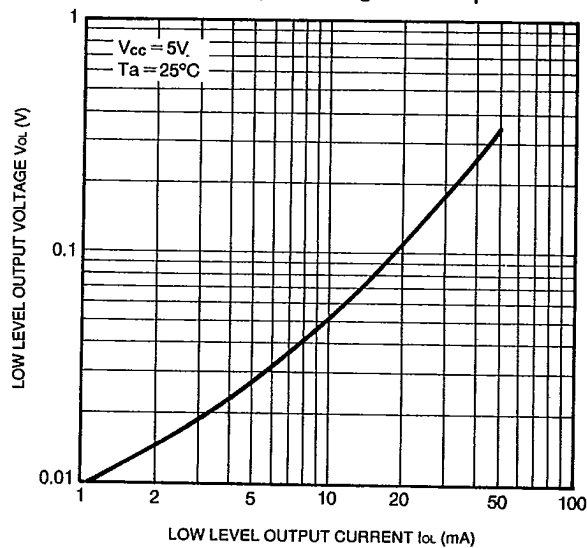


Figure 7: Threshold Input Current vs. Supply Voltage

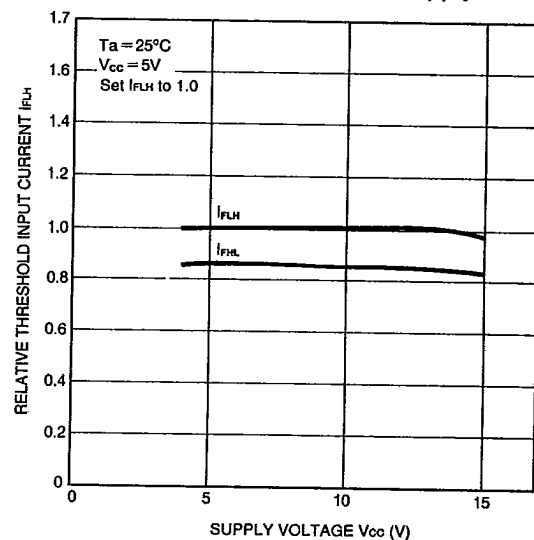


Figure 8: Supply Current vs. Temperature

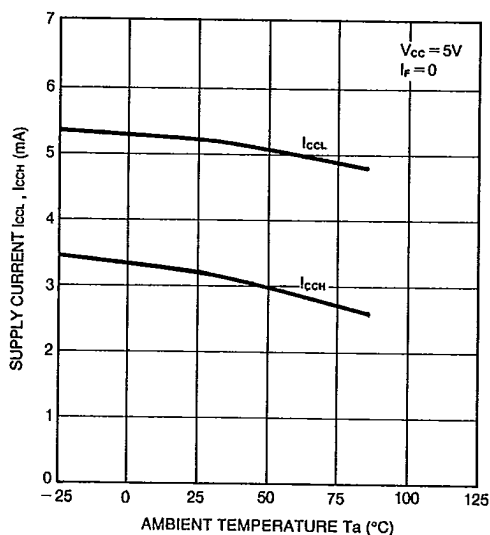
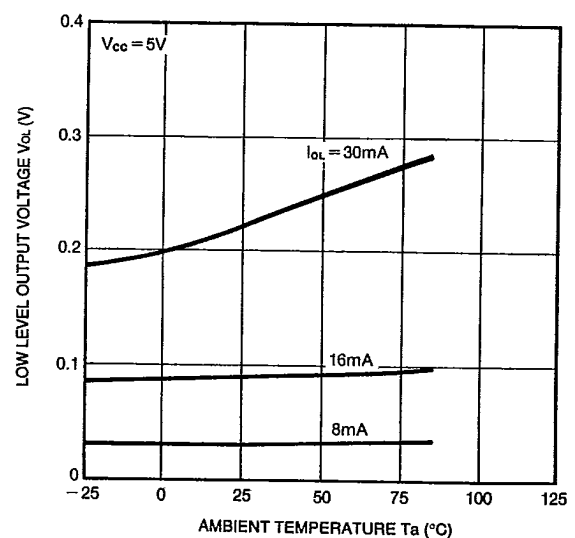


Figure 9: Low Level Output Voltage vs. Temperature



PHOTOREFLECTOR P3062-01

Figure 10: Threshold Input Current vs. Temperature

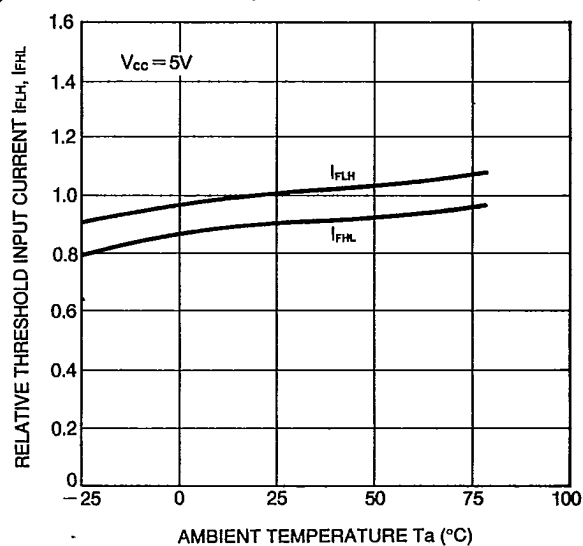


Figure 11: Propagation Delay Time vs. Forward Current

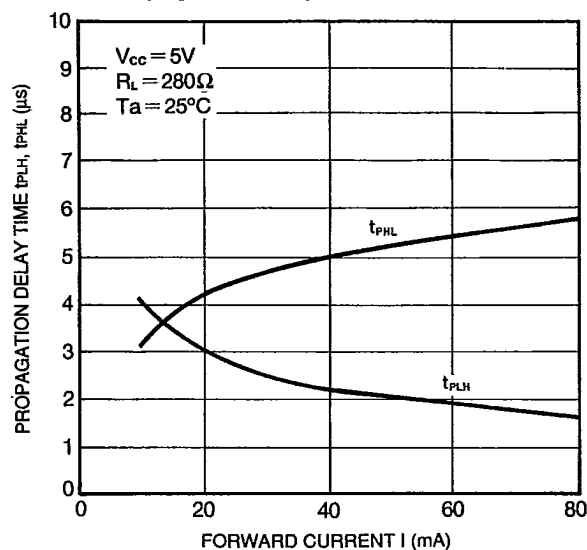


Figure 12: Rise/Fall Time vs. Load Resistance

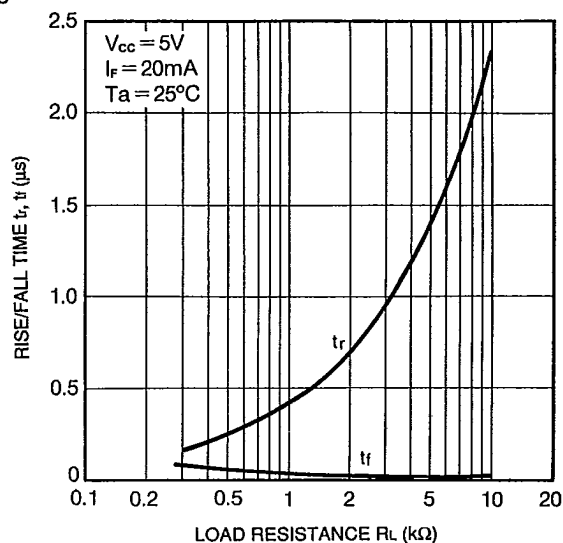


Figure 13: Position Detection Characteristic (1)

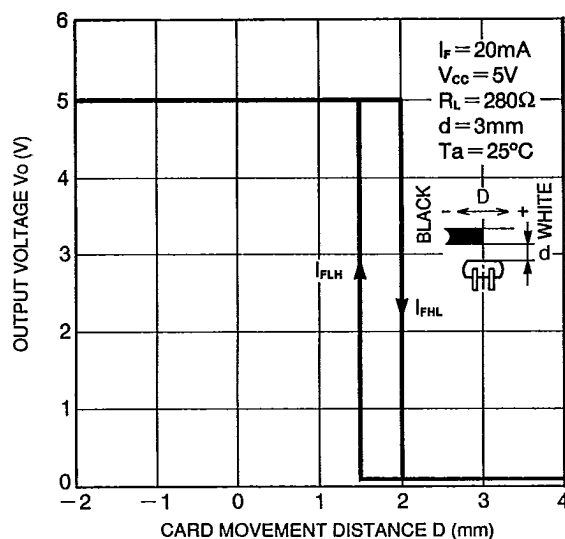


Figure 14: Position Detection Characteristic (2)

